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The Manufacturing Technology of Continuous Glass Fibres - III

Third Completely Revised Edition

by **K.L. Loewenstein**

Glass Science and Technology Volume 6

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These are just a couple of the many favourable reviews which greeted the appearance of the first edition of Dr. Loewenstein's book in 1973. Since the first edition, technical development has evolved rapidly, and the fields of application are expanding continuously. The industry has become very competitive. Glass fibre now costs less (in money terms) than it did 30 years ago. At the same time, quality standards are higher. This has been achieved by significant advances in technology, improving the scale of manufacturing operations and increased automation, while being subjected, at the same time, to increasingly severe legislation designed to protect the environment.

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Stimulated Deposition Processes and Materials Aspects of Ion Beam Synthesis

Proceedings of Symposium C and Symposium G of the 1993 E-MRS Spring Conference, Strasbourg, France, 4-7 May 1993

Edited by **H. Freller**†, **J.M. Martínez-Duart**, **Y. Pauleau**, **J. Dieleman**, **P.L.F. Hemment** and **J.A. Kilner**

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This volume contains the proceedings of Symposium C: Ion Beam, Plasma, Laser, and Thermally-Stimulated Deposition Processes and Symposium G: Material Aspects of Ion Beam Synthesis: Phase Formation and Modification of the E-MRS 1993 Spring conference.
Symposium C covers recent trends in the field of deposition processes stimulated by low energy particle beams and shows the wide range of materials which can be modified advantageously by energetic ion and photon bombardment. Topics covered include: sputter-deposition processes; low energy ion-assisted deposition processes and thermally-activitated CVD processes; ion beam-assisted deposition and laser beam-induced modifications of materials.
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(3) all authors have made a significant contribution to the research reported and have read and approved the manuscript which has been submitted. All authors take full responsibility for the published paper.

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(i) **Abstract.** A brief reprise of the contents of the manuscript, containing specific results and conclusions.

(ii) **Introduction.** Justifications for the research, hypotheses to be tested by the experiments or theory, and a review of the literature relevant to be reported.

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Handbook of Glass Data

By **O.V. Mazurin, M.V. Streltsina** and **T.P. Shvaiko-Shvaikovskaya**

Part E: Single-Component, Binary, and Ternary Oxide Glasses

Supplements to Parts A, B, C and D

Physical Sciences Data Volume 15E

The present volume is the fifth (and the last) part of the Handbook of Glass Data. Parts A-D covered properties of all single-component, binary and ternary oxide glasses and glass-forming melts. In the present part of the Handbook all the appropriate data published in the world literature since the preparation of the previous parts and until the end of 1990 are compiled.

The principles of data selection and presentation applied when compiling Part E were as follows:

1. The book covers information on systems capable of forming glasses by cooling melts.
2. The data on melt properties are presented only for the glass-forming systems. Nevertheless, data are presented on melt properties over the whole range of concentrations, irrespective of whether this range is limited by a glass-forming region or not.
3. The notion of a *"component"*, which is very important for determining the number of components in each glass, is defined by the authors in the following way:
(a) An oxide entering into the composition of a glass is considered a component.
(b) If an analytical composition of a glass is given with impurities, these impurities are not to be taken into consideration when classifying glasses with respect to the number of components if there is no reason to believe that the given impurities considerably change the corresponding property.
4. Data on the crystallization rate of glasses are included since this characteristic should be considered as one of the most important properties of a glass.
5. In most cases, data on the so-called characteristic temperatures (deformation temperatures, upper and lower annealing points and others) are not given. Littleton's softening temperatures and glass transition temperatures are the main exceptions. According to Littleton the softening temperature conforms to the viscosity of $10^{7.65}$ poises, although it is possible that drastic composition variations may lead to some changes in this value.
6. When the original papers report viscosity and electrical conductivity logarithms accurate to three or four decimal places, the figures are rounded off to two decimal places, since with present experimental techniques a minimum measurement error of the indicated properties exceeds ± 2% of a measured value even in the best investigations.

In this volume all systems are united into large groups according to the valence of the elements forming the corresponding oxides. The sequence is as follows: glass formation, crystallization, density, thermal expansion and other thermal properties, optical properties, viscosity, elastic properties and internal friction, strength, surface tension, chemical durability, electrical properties, diffusion, permeation and solubility of gases, ion diffusion, volatility and magnetic properties. The experimental data are given in chronological order and data on glass properties are given in tabular form.

This handbook will be of vital interest to all those working in research laboratories of glass-making firms, university lecturers and students at undergraduate and postgraduate level involved with materials science.

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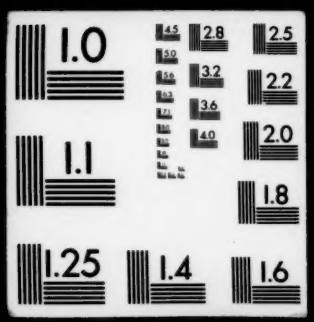
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